

Trying 11180...Open

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PLEASE ENTER HOST PORT ID:  
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## TFTHYDRO,TRN

FILE 'USPAT' ENTERED AT 14:36:20 ON 09 DEC 1998

=> s ccd and crystallized silicon

23104 CCD  
45636 CRYSTALLIZED  
195699 SILICON  
.. 223 CRYSTALLIZED SILICON  
..... (CRYSTALLIZED(W) SILICON)  
11 CCD AND CRYSTALLIZED SILICON

=> d 11 1-6

1. 5,846,318, Dec. 8, 1998, Method and system for controlling growth of a silicon crystal; Massoud Javidi, 117/14, 13, 15, 16, 201, 202, 208 [IMAGE AVAILABLE]
  2. 5,824,235, Oct. 20, 1998, Method of manufacturing semiconductor device; Shunpei Yamazaki, et al., 216/23, 13, 18, 67; 438/720 [IMAGE AVAILABLE]
  3. 5,667,585, Sep. 16, 1997, Method for the preparation of wire-formed silicon crystal; Tsuguo Fukuda, et al., 117/49, 52, 75, 87 [IMAGE AVAILABLE]
  4. 5,591,988, Jan. 7, 1997, Solid state imaging device with low trap density; Michio Arai, et al., 257/59, 66, 72, 291, 292; 438/60, 97; 166 [IMAGE AVAILABLE]
  5. 5,582,640, Dec. 10, 1996, Semiconductor device and its fabricating method; Takako Okada, et al., 117/8, 930; 438/166, 481, 486 [IMAGE AVAILABLE]
  6. 5,574,293, Nov. 12, 1996, Solid state imaging device using disilane; Michio Arai, et al., 438/59; 257/59, 66, 72, 291, 292; 438/96, 166 [IMAGE AVAILABLE]

=> d 11 7-11

  7. 5,302,230, Apr. 12, 1994, Heat treatment by light irradiation; Masumitsu Ino, et al., 117/92, 88, 904 [IMAGE AVAILABLE]
  8. 4,809,075, Feb. 28, 1989, Solid-state imaging device having an amplifying means in the matrix arrangement of picture elements; Hajime Akimoto, et al., 348/301, 241, 310 [IMAGE AVAILABLE]
  9. 4,598,305, Jul. 1, 1986, Depletion mode thin film semiconductor photodetectors; Anne Chiang, et al., 257/66, 216, 226, 291, 292, 348, 402, 443 [IMAGE AVAILABLE]
  10. 4,523,214, Jun. 11, 1985, Solid state image pickup device utilizing microcrystalline and amorphous silicon; Masataka Hirose, et al., 257/443, 53, 74, 76, 458; 438/60, 96 [IMAGE AVAILABLE]
  11. 4,358,326, Nov. 9, 1982, Epitaxially extended polycrystalline structures utilizing a predeposit of amorphous silicon with subsequent annealing; Ven Y. Doo, 438/585; 148/DIG.3, DIG.26, DIG.122, DIG.123, DIG.164; 257/756; 438/396, 481, 486, 587, 660, 684 [IMAGE AVAILABLE]

=> d 11 1-11 pn

US PAT NO:	5,846,318 [IMAGE AVAILABLE]	L1: 1 of 11
US PAT NO:	5,824,235 [IMAGE AVAILABLE]	L1: 2 of 11
US PAT NO:	5,667,585 [IMAGE AVAILABLE]	L1: 3 of 11
US PAT NO:	5,591,988 [IMAGE AVAILABLE]	L1: 4 of 11
US PAT NO:	5,582,640 [IMAGE AVAILABLE]	L1: 5 of 11
US PAT NO:	5,574,293 [IMAGE AVAILABLE]	L1: 6 of 11
US PAT NO:	5,302,230 [IMAGE AVAILABLE]	L1: 7 of 11
US PAT NO:	4,809,075 [IMAGE AVAILABLE]	L1: 8 of 11
US PAT NO:	4,598,305 [IMAGE AVAILABLE]	L1: 9 of 11
US PAT NO:	4,523,214 [IMAGE AVAILABLE]	L1: 10 of 11
US PAT NO:	4,358,326 [IMAGE AVAILABLE]	L1: 11 of 11